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27/14603 (2013.01)(57) **ABSTRACT**

A solid-state imaging element according to the present disclosure includes a first light receiving pixel, a second light receiving pixel, and a metal layer. The first light receiving pixel receives visible light. The second light receiving pixel receives infrared light. The metal layer is provided to face at least one of a photoelectric conversion unit of the first light receiving pixel and a photoelectric conversion unit of the second light receiving pixel on an opposite side of a light incident side, and contains tungsten as a main component.

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